

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of forming a thin film pattern by placing a functional liquid on a substrate, comprising:

a bank formation step of forming banks in accordance with the thin film pattern on the substrate;

a residue processing step of removing residue between the banks; and

a material placement step of placing the functional liquid between the banks removed the ~~residue~~residue,

wherein the residue processing step comprises a photo irradiation processing step.

2. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step comprises a step of removing residue in bottom portions between the banks.

3-8. (Canceled)

9. (Original) A method of forming a thin film pattern according to claim 1, further comprising a repellency processing step of imparting repellency to the banks after the residue processing step.

10. (Original) A method of forming a thin film pattern according to claim 9, further comprising a step of removing residue from bottom portions between the banks after the repellency processing step of imparting repellency to the banks.

11. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a step of removing residue from bottom portions between the banks.

12. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a photo irradiation processing step.

13. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas.

14. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas and a photo irradiation processing step.

15. (Original) A method of forming a thin film pattern according to claim 10, wherein the residue processing step performs etching using acid.

16. (Original) A method of forming a thin film pattern according to claim 1, wherein the residue processing step is performed once again after the material placement step.

17. (Original) A method of forming a thin film pattern according to claim 1, wherein the functional liquid exhibits electroconductivity after undergoing heat processing or light processing.

18. (Original) A method of forming a thin film pattern according to claim 1, wherein the functional liquid contains electroconductive fine particles.

19-21. (Canceled)

22. (Currently Amended) A method of manufacturing an active matrix substrate comprising:

a first step of forming a gate wire on a substrate;

a second step of forming a gate insulating film on the gate wire;

a third step of laminating a semiconductor layer via the gate insulating film;

a fourth step of forming a source electrode and drain electrode on the gate insulating film;

a fifth step of placing a non-conductive material on the source electrode and the drain electrode;

a sixth step of forming a pixel electrode after the placement of the insulating material,

wherein at least one of the first, fourth, and sixth steps further comprising:

a bank forming step of forming banks to correspond to a formation pattern;

a residue processing step of removing residue between the banks; and

a material placement step of placing a functional material between the banks removed the residue by being discharged using a droplet discharge ~~apparatus~~apparatus,

wherein the residue processing step comprises a photo irradiation processing step.

23. (New) A method of manufacturing an active matrix substrate according to claim 22, further comprising a repellency processing step of imparting repellency to the banks after the residue processing step.

24. (New) A method of manufacturing an active matrix substrate according to claim 23, further comprising removing residue from bottom portions between the banks after the repellency processing step of imparting repellency to the banks.

25. (New) A method of manufacturing an active matrix substrate according to claim 23, wherein the residue processing step that is performed after the repellency processing step comprises a step of removing residue from bottom portions between the banks.

26. (New) A method of manufacturing an active matrix substrate according to claim 23, wherein the residue processing step that is performed after the repellency processing step comprises a photo irradiation processing step.

27. (New) A method of manufacturing an active matrix substrate according to claim 23, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas.

28. (New) A method of manufacturing an active matrix substrate according to claim 23, wherein the residue processing step that is performed after the repellency processing step comprises a plasma processing step that uses a predetermined processing gas and a photo irradiation processing step.

29. (New) A method of manufacturing an active matrix substrate according to claim 23, wherein the residue processing step performs etching using acid.

30. (New) A method of manufacturing an active matrix substrate according to claim 22, wherein the residue processing step is performed once again after the material placement step.